

4.5V 至 18V 输入、5.5A 同步降压转换器

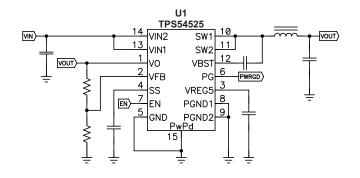
查询样品: TPS54525

特性

- D-CAP2™ 模式支持快速瞬态响应
- 低输出纹波并支持陶瓷输出电容器
- 宽泛的 V_{IN}输入电压范围: 4.5V 至 18V
- 输出电压范围: 0.76V 至 5.5V
- 高效率集成型场效应晶体管 (FET) 针对更低占空比应用进行了优化
 -63 mΩ(高侧)与 33 mΩ(低侧)
- 关断时的高效率,流耗不足 10µA
- 高初始带隙参考精度
- 可调软启动
- 预偏置软启动
- 650-kHz 开关频率 (f_{sw})
- 逐周期限流
- 电源良好输出

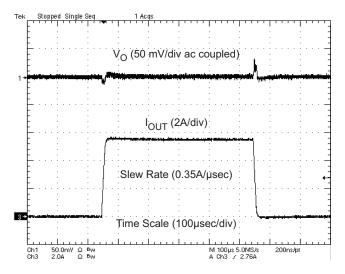
应用

- 低电压系统的广泛应用
 - 数字电视电源
 - 高清 Blu-ray Disc™ 播放器
 - 网络家庭终端设备
 - 数字机顶盒 (STB)



说明

TPS54525 是一款自适应接通时间 D-CAP2™ 模式同步降压转换器。 TPS54525 可帮助系统设计人员通过低成本、低组件数量的低待机电流解决方案来完成各种终端设备的电源总线调节器集。 TPS54525 的主控制环路使用 D-CAP2™ 模式控制,此控制方式提供一个无需外部补偿组件的极快速瞬态响应。 TPS54525 的专有电路还有助于该器件适应诸如 POSCAP 或 SP-CAP 等低等效串联电阻 (ESR) 输出电容器以及超低 ESR 陶瓷电容器。 该器件的工作输入电压介于 4.5V至 18V VIN 之间。 输出电压可在 0.76 V 与 5.5 V 之间进行编程。该器件还特有一个可调软启动时间和一个电源正常功能。 TPS54525 采用 14 引脚散热薄型小外形尺寸 (HTSSOP) 封装,设计工作温度介于 -40℃ 到 85°C 之间。



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This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

T _A	PACKAGE ^{(2) (3)}	ORDERABLE PART NUMBER	PIN	TRANSPORT MEDIA, QUANTITY
45°C to 05°C	PowerPAD™	TPS54525PWP	4.4	Tube
–45°C to 85°C	(HTSSOP) – PWP	TPS54525PWPR	14	Tape and Reel

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (3) All package options have Cu NIPDAU lead/ball finish.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
	VIN1, VIN2 EN	-0.3	20	V
	VBST	-0.3	26	V
Input voltage range,	VBST (10 ns transient)	-0.3	28	V
	VBST (vs SW1, SW2)	-0.3	6.5	V
	VFB, VO, SS, PG	-0.3	6.5	V
	SW1, SW2	-2	20	V
	SW1, SW2 (10 ns transient)	-3	22	V
Output voltage renge	VREG5	-0.3	6.5	V
Output voltage range	PGND1, PGND2	-0.3	0.3	V
Voltage from GND to Powe	erPAD™, V _{diff}	-0.2	0.2	V
	Human Body Model (HBM)		2	kV
Electrostatic discharge	Charged Device Model (CDM)		500	V
Operating junction tempera	iture, T _J	-40	150	°C
Storage temperature, T _{stg}		-55	150	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

		TPS54525	
	THERMAL METRIC ⁽¹⁾	PWP	UNITS
		14 PINS	
θ_{JA}	Junction-to-ambient thermal resistance	43.7	
θ_{JCtop}	Junction-to-case (top) thermal resistance	33.1	
θ_{JB}	Junction-to-board thermal resistance	28.4	8004
Ψлт	Junction-to-top characterization parameter	1.3	°C/W
ΨЈВ	Junction-to-board characterization parameter	28.2	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	4.7	1

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{IN}	Supply input voltage range		4.5	18	V
		VBST	-0.3	24	
		VBST(10 ns transient)	-0.3	27	
		VBST (vs SW1, SW2)	-0.3	5.7	
		SS, PG	-0.3	5.7	
VI	Input voltage range	EN	-0.3	18	V
		VO, VFB	-0.3	5.5	
		SW1, SW2	-1.8	18	
		SW1, SW2 (10 ns transient)	-3	21	
		PGND1, PGND2	-0.3	0.1	
Vo	Output voltage range	VREG5	-0.3	5.7	V
lo	Output Current range	I _{VREG5}	0	5	mA
T _A	Operating free-air temperature		-40	85	°C
TJ	Operating junction temperature		-40	150	°C

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range, V_{IN} = 12V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT		•			
I _{VIN}	Operating - non-switching supply current	Operating - non-switching supply current V_{IN} current, $T_A = 25^{\circ}C$, $EN = 5 \text{ V}$, $V_{VFB} = 0.8 \text{ V}$		900	1400	μA
I _{VINSDN}	Shutdown supply current	V _{IN} current, T _A = 25°C, EN = 0 V		3.6	10	μΑ
LOGIC TI	HRESHOLD					
V _{ENH}	EN high-level input voltage		1.6			V
V _{ENL}	EN low-level input voltage				0.6	V
R _{EN}	EN pin resistance to GND	V _{EN} = 12 V	220	440	880	kΩ
VFB VOL	TAGE AND DISCHARGE RESISTANCE		•			
		$T_A = 25$ °C, $V_O = 1.05$ V, continuous mode	757	765	773	
V _{FBTH} VFB threshold voltage		$T_A = -40$ °C to 85°C, $V_O = 1.05$ V, continuous mode ⁽¹⁾	754		776	mV
I _{VFB}	VFB input current	V _{VFB} = 0.8 V, T _A = 25°C		0	±0.15	μΑ
R _{Dischg}	V _O discharge resistance	V _{EN} = 0 V, V _O = 0.5 V, T _A = 25°C		50	100	Ω
VREG5 O	UTPUT		•			
V _{VREG5}	VREG5 output voltage	T _A = 25°C, 6.0 V < V _{IN} < 18 V, 0 < I _{VREG5} < 5 mA	5.2	5.5	5.7	V
V _{VREG5}	VREG5 Line regulation	6.0 V < V _{IN} < 18 V, I _{VREG5} = 5 mA			20	mV
V _{VREG5}	VREG5 Load regulation	0 mA < I _{VREG5} < 5 mA			100	mV
I _{VREG5}	VREG5 Output current	V _{IN} = 6 V, V _{VREG5} = 4 V, T _A = 25°C		60		mA
MOSFET						
R _{dsonh}	High side switch resistance	T _A = 25°C, V _{BST} - V _{SW1,2} = 5.5 V		63		mΩ
R _{dsonl}	Low side switch resistance	T _A = 25°C		33		mΩ

⁽¹⁾ Not production tested.



ELECTRICAL CHARACTERISTICS (continued)

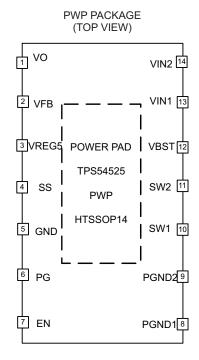
over operating free-air temperature range, $V_{\rm IN}$ = 12V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURREN	T LIMIT	·		-		
I _{ocl}	Current limit	L _{OUT} = 1.5 μH ⁽²⁾	6.1	6.9	8.4	Α
THERMA	L SHUTDOWN		<u>"</u>			
_		Shutdown temperature (2)		165		
T _{SDN}	Thermal shutdown threshold	Hysteresis (2)		35		°C
ON-TIME	TIMER CONTROL	·		-		
T _{ON}	On time	V _{IN} = 12 V, V _O = 1.05 V		155		ns
T _{OFF(MIN)}	Minimum off time	T _A = 25°C, V _{VFB} = 0.7 V		260	330	ns
SOFT ST	ART					
I _{SSC}	SS charge current	V _{SS} = 1 V	4.2	6.0	7.8	μΑ
I _{SSD}	SS discharge current	V _{SS} = 0.5 V	0.1	0.2		mA
POWER (GOOD	•	•			
\ /	DC through ald	V _{VFB} rising (good)	85	90	95	%
V_{THPG}	PG threshold	V _{VFB} falling (fault)		85		%
I _{PG}	PG sink current	V _{PG} = 0.5 V	2.5	5		mA
OUTPUT	UNDERVOLTAGE AND OVERVOLTA	AGE PROTECTION	·		·	
V _{OVP}	Output OVP trip threshold	OVP detect	120	125	130	%
T _{OVPDEL}	Output OVP prop delay			10		μs
\ /	Outroot IN/D trin through ald	UVP detect	60	65	70	%
V_{UVP}	Output UVP trip threshold	Hysteresis		10		%
T _{UVPDEL}	Output UVP delay			0.25		ms
T _{UVPEN}	Output UVP enable delay	Relative to soft-start time		x 1.7		
UVLO						
		Wake up VREG5 voltage	3.31	3.61	3.91	
V_{UVLO}	UVLO threshold	Fall VREG5 voltage	2.82	3.12	3.42	V
		Hysteresis VREG5 voltage	0.37	0.49	0.61	

⁽²⁾ Not production tested.



DEVICE INFORMATION

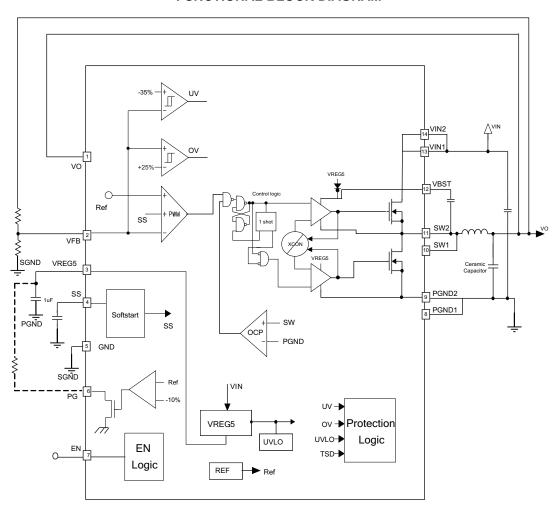


PIN FUNCTIONS

		FIN FUNCTIONS
PIN		DESCRIPTION
NAME	NO.	DESCRIPTION
VO	1	Connect to output of converter. This pin is used for output discharge function.
VFB	2	Converter feedback input. Connect to output voltage with feedback resistor divider.
VREG5	3	$5.5~V$ power supply output. A capacitor (typical 1 μ F) should be connected to GND. VREG5 is not active when EN is low.
SS	4	Soft-start control. An external capacitor should be connected to GND.
GND	5	Signal ground pin
PG	6	Open drain power good output
EN	7	Enable control input. EN is active high and must be pulled up to enable the device.
PGND1, PGND2	8, 9	Ground returns for low-side MOSFET. Also serve as inputs of current comparators. Connect PGND and GND strongly together near the IC.
SW1, SW2	10, 11	Switch node connection between high-side NFET and low-side NFET. Also serve as inputs to current comparators.
VBST	12	Supply input for high-side NFET gate driver (boost terminal). Connect capacitor from this pin to respective SW1, SW2 terminals. An internal PN diode is connected between VREG5 to VBST pin.
VIN1, VIN2	13, 14	Power input and connected to high side NFET drain. Supply input for 5-V internal linear regulator for the control circuitry.
PowerPAD™	Back side	Thermal pad of the package. Must be soldered to achieve appropriate dissipation. Should be connected to PGND.



FUNCTIONAL BLOCK DIAGRAM





OVERVIEW

The TPS54525 is a 5.5-A synchronous step-down (buck) converter with two integrated N-channel MOSFETs. It operates using D-CAP2™ mode control. The fast transient response of D-CAP2™ control reduces the output capacitance required to meet a specific level of performance. Proprietary internal circuitry allows the use of low ESR output capacitors including ceramic and special polymer types.

DETAILED DESCRIPTION

PWM Operation

The main control loop of the TPS54525 is an adaptive on-time pulse width modulation (PWM) controller that supports a proprietary D-CAP2™ mode control. D-CAP2™ mode control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output.

At the beginning of each cycle, the high-side MOSFET is turned on. This MOSFET is turned off after internal one shot timer expires. This one shot is set by the converter input voltage, VIN, and the output voltage, VO, to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The one-shot timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the reference voltage. An internal ramp is added to reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2TM mode control.

PWM Frequency and Adaptive On-Time Control

TPS54525 uses an adaptive on-time control scheme and does not have a dedicated on board oscillator. The TPS54525 runs with a pseudo-constant frequency of 650 kHz by using the input voltage and output voltage to set the on-time one-shot timer. The on-time is inversely proportional to the input voltage and proportional to the output voltage, therefore, when the duty ratio is VOUT/VIN, the frequency is constant.

Soft Start and Pre-Biased Soft Start

The soft start function is adjustable. When the EN pin becomes high, $6-\mu A$ current begins charging the capacitor which is connected from the SS pin to GND. Smooth control of the output voltage is maintained during start up. The equation for the slow start time is shown in Equation 1. VFB voltage is 0.765 V and SS pin source current is $6 \mu A$.

$$t_{SS}(ms) = \frac{C_{SS}(nF) \times V_{REF} \times 1.1}{I_{SS}(\mu A)} = \frac{C_{SS}(nF) \times 0.765 \times 1.1}{6}$$
(1)

The TPS54525 contains a unique circuit to prevent current from being pulled from the output during startup if the output is pre-biased. When the soft-start commands a voltage higher than the pre-bias level (internal soft start becomes greater than feedback voltage V_{FB}), the controller slowly activates synchronous rectification by starting the first low side FET gate driver pulses with a narrow on-time. It then increments that on-time on a cycle-bycycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-bias output, and ensure that the out voltage (VO) starts and ramps up smoothly into regulation and the control loop is given time to transition from pre-biased start-up to normal mode operation.

Power Good

The TPS54525 has power-good open drain output. The power good function is activated after soft start has finished. The power good function becomes active after 1.7 times soft-start time. When the output voltage is within -10% of the target value, internal comparators detect power good state and the power good signal becomes high. Rpg resister value ,which is connected between PG and VREG5, is required from $25k\Omega$ to $150k\Omega$. If the feedback voltage goes under 15% of the target value, the power good signal becomes low.



VREG5

VREG5 is an internally generated voltage source used by the TPS54525. It is derived directly from the input voltage and is nominally regulated to 5.5 V when the input voltage is above 5.6 V. The output of the VREG5 regulator is the input to the internal UVLO function. VREG5 must be above the UVLO wake up threshold voltage (3.6 V typical) for the TPS54525 to function. Connect a 1 μ F capacitor between pin 3 of the TPS54525 and power ground for proper regulation of the VREG5 output. The VREG5 output voltage is available for external use. It is recommended to use no more than 5 mA for external loads. The VREG5 output is disabled when the TPS54525 EN pin is open or pulled low.

Output Discharge Control

TPS54525 discharges the output when EN is low, or the controller is turned off by the protection functions (OVP, UVP, UVLO and thermal shutdown). The output is discharged by an internal $50-\Omega$ MOSFET which is connected from VO to PGND. The internal low-side MOSFET is not turned on during the output discharge operation to avoid the possibility of causing negative voltage at the output.

Current Protection

The output overcurrent protection (OCP) is implemented using a cycle-by-cycle valley detect control circuit. The switch current is monitored by measuring the low-side FET switch voltage between the SW pin and GND. This voltage is proportional to the switch current. To improve accuracy, the voltage sensing is temperature compensated.

During the on time of the high-side FET switch, the switch current increases at a linear rate determined by V_{IN} , V_{OUT} , the on-time and the output inductor value. During the on time of the low-side FET switch, this current decreases linearly. The average value of the switch current is the load current I_{OUT} . If the measured voltage is above the voltage proportional to the current limit, Then , the device constantly monitors the low-side FET switch voltage, which is proportional to the switch current, during the low-side on-time.

The converter maintains the low-side switch on until the measured voltage is below the voltage corresponding to the current limit at which time the switching cycle is terminated and a new switching cycle begins. In subsequent switching cycles, the on-time is set to a fixed value and the current is monitored in the same manner.

There are some important considerations for this type of overcurrent protection. The load current one half of the peak-to-peak inductor current higher than the overcurrent threshold. Also when the current is being limited, the output voltage tends to fall as the demanded load current may be higher than the current available from the converter. This may cause the output undervoltage protection circuit to be activated. When the over current condition is removed, the output voltage returns to the regulated value. This protection is non-latching.

Over/Under Voltage Protection

TPS54525 monitors a resistor divided feedback voltage to detect over and under voltage. When the feedback voltage becomes higher than 125% of the target voltage, the OVP comparator output goes high and the circuit latches as both the high-side and low-side MOSFET drivers turn off. When the feedback voltage becomes lower than 65% of the target voltage, the UVP comparator output goes high and an internal UVP delay counter begins. After 250 μ s, the device latches off both internal top and bottom MOSFET. This function is enabled approximately 1.7 x softstart time.

UVLO Protection

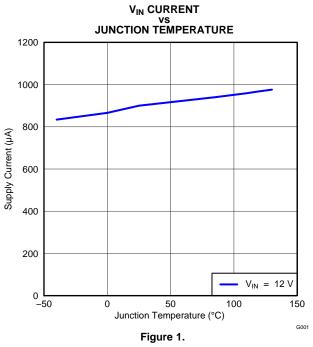
Undervoltage lock out protection (UVLO) monitors the voltage of the V_{REG5} pin. When the V_{REG5} voltage is lower than UVLO threshold voltage, the TPS54525 is shut off. This is protection is non-latching.

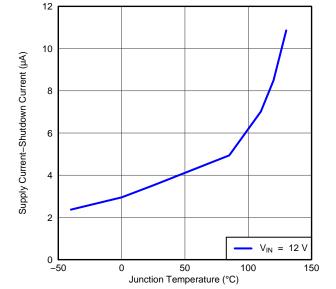
Thermal Shutdown

TPS54525 monitors the temperature of itself. If the temperature exceeds the threshold value (typically 165°C), the device is shut off. This is non-latch protection.



 V_{IN} = 12 V, T_A = 25 °C (unless otherwise noted)



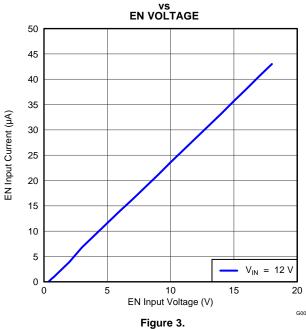


V_{IN} SHUTDOWN CURRENT vs JUNCTION TEMPERATURE





Figure 2.



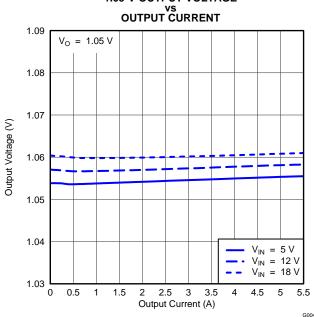
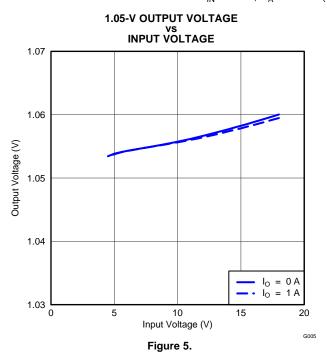


Figure 4.



 V_{IN} = 12 V, T_A = 25 °C (unless otherwise noted)



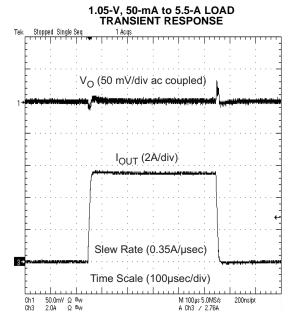
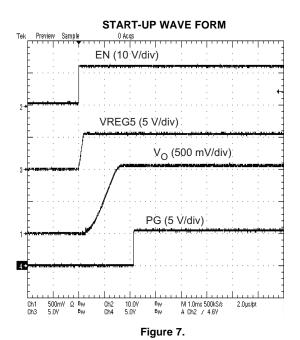
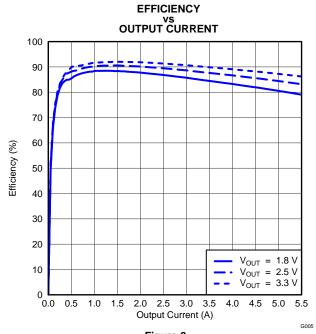


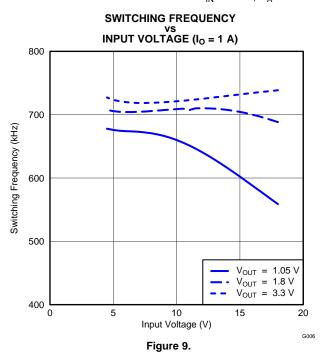
Figure 6.

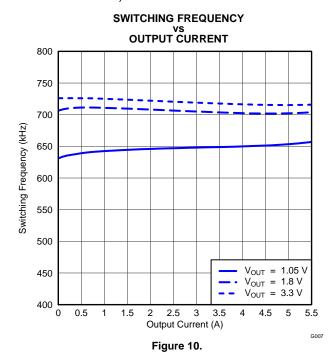






 V_{IN} = 12 V, T_A = 25 °C (unless otherwise noted)





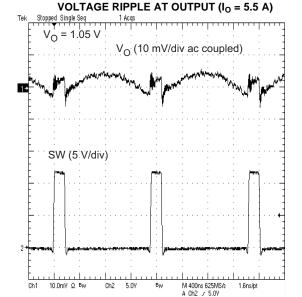
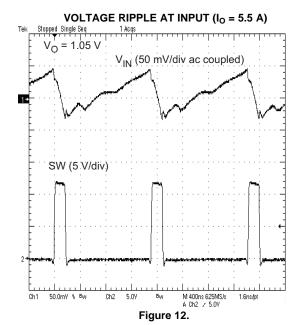


Figure 11.





 V_{IN} = 12 V, T_A = 25 °C (unless otherwise noted)

Figure 13.



DESIGN GUIDE

Step By Step Design Procedure

To begin the design process, you must know a few application parameters:

- Input voltage range
- Output voltage
- Output current
- Output voltage ripple
- Input voltage ripple

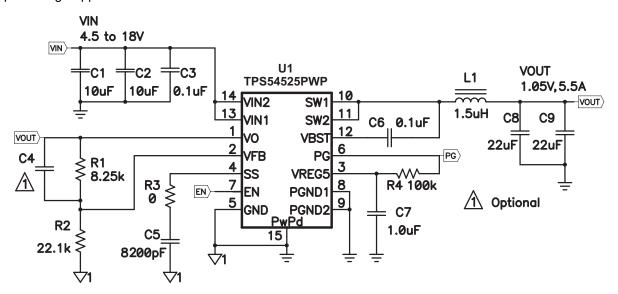


Figure 14. Shows the schematic diagram for this design example.

Output Voltage Resistors Selection

The output voltage is set with a resistor divider from the output node to the VFB pin. It is recommended to use 1% tolerance or better divider resistors. Start by using Equation 2 to calculate V_{OUT} .

To improve efficiency at very light loads consider using larger value resistors, too high of resistance will be more susceptible to noise and voltage errors from the VFB input current will be more noticeable.

$$V_{OUT} = 0.765 \cdot \left(1 + \frac{R1}{R2}\right) \tag{2}$$

Output Filter Selection

The output filter used with the TPS54525 is an LC circuit. This LC filter has double pole at:

$$F_P = \frac{1}{2\pi\sqrt{L_{OUT} \times C_{OUT}}}$$
(3)

At low frequencies, the overall loop gain is set by the output set-point resistor divider network and the internal gain of the TPS54525. The low frequency phase is 180 degrees. At the output filter pole frequency, the gain rolls off at a -40 dB per decade rate and the phase drops rapidly. D-CAP2™ introduces a high frequency zero that reduces the gain roll off to -20 dB per decade and increases the phase to 90 degrees one decade above the zero frequency. The inductor and capacitor selected for the output filter must be selected so that the double pole of Equation 3 is located below the high frequency zero but close enough that the phase boost provided be the high frequency zero provides adequate phase margin for a stable circuit. To meet this requirement use the values recommended in Table 1



Table 1. Recommended Component Values

Output Voltage (V)	R1 (kΩ)	R2 (kΩ)	C4 (pF) ⁽¹⁾	L1 (µH)	C8 + C9 (µF)
1	6.81	22.1		1.0 - 1.5	22 - 68
1.05	8.25	22.1		1.0 - 1.5	22 - 68
1.2	12.7	22.1		1.0 - 1.5	22 - 68
1.5	21.5	22.1		1.5	22 - 68
1.8	30.1	22.1	5 - 22	1.5	22 - 68
2.5	49.9	22.1	5 - 22	2.2	22 - 68
3.3	73.2	22.1	5 - 22	2.2	22 - 68
5	124	22.1	5 - 22	3.3	22 - 68

(1) Optional

For higher output voltages at or above 1.8 V, additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1.

Since the DC gain is dependent on the output voltage, the required inductor value will increase as the output voltage increases. For higher output voltages at or above 1.8 V, additional phase boost can be achieved by adding a feed forward capacitor (C4) in parallel with R1

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using Equation 4, Equation 5 and Equation 6. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current. Use 650 kHz for f_{SW} .

Use 650 kHz for f_{SW} . Make sure the chosen inductor is rated for the peak current of Equation 5 and the RMS current of Equation 6.

$$Ilp - p = \frac{V_{OUT}}{V_{IN\,(max)}} \bullet \frac{V_{IN\,(max)} - V_{OUT}}{L_O \bullet f_{SW}}$$

$$\tag{4}$$

$$I_{lpeak} = I_O + \frac{Ilp - p}{2} \tag{5}$$

$$I_{Lo(RMS)} = \sqrt{I_O^2 + \frac{1}{12} I l p - p^2}$$
 (6)

For this design example, the calculated peak current is 6.01 A and the calculated RMS current is 5.5 A. The inductor used is a TDK SPM6530-1R5M100 with a peak current rating of 11.5 A and an RMS current rating of 11 A

The capacitor value and ESR determines the amount of output voltage ripple. The TPS54525 is intended for use with ceramic or other low ESR capacitors. Recommended values range from 22uF to 68uF. Use Equation 7 to determine the required RMS current rating for the output capacitor.

$$I_{CO(RMS)} = \frac{V_{OUT} \bullet (V_{IN} - V_{OUT})}{\sqrt{12} \bullet V_{IN} \bullet L_O \bullet f_{SW}}$$

$$(7)$$

For this design two TDK C3216X5R0J226M 22uF output capacitors are used. The typical ESR is 2 m Ω each. The calculated RMS current is 0.284 A and each output capacitor is rated for 4A.

Input Capacitor Selection

The TPS54525 requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A ceramic capacitor over 10 μ F is recommended for the decoupling capacitor. An additional 0.1 μ F capacitor from pin 14 to ground is recommended to improve the EMI performance. The capacitor voltage rating needs to be greater than the maximum input voltage.

Bootstrap Capacitor Selection

A 0.1 μ F ceramic capacitor must be connected between the VBST to SW pin for proper operation. It is recommended to use a ceramic capacitor.



VREG5 Capacitor Selection

A 1.0 μF ceramic capacitor must be connected between the VREG5 to GND pin for proper operation. It is recommended to use a ceramic capacitor.

THERMAL INFORMATION

This PowerPad™ package incorporates an exposed thermal pad that is designed to be directly to an external heartsick. The thermal pad must be soldered directly to the printed board (PCB). After soldering, the PCB can be used as a heartsick. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heartsick structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD™ package and how to use the advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD™ Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD™ Made Easy, Texas Instruments Literature No. SLMA004.

The exposed thermal pad dimensions for this package are shown in the following illustration.

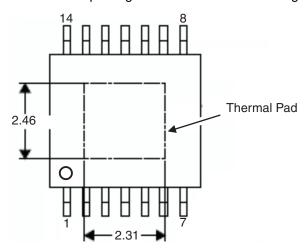


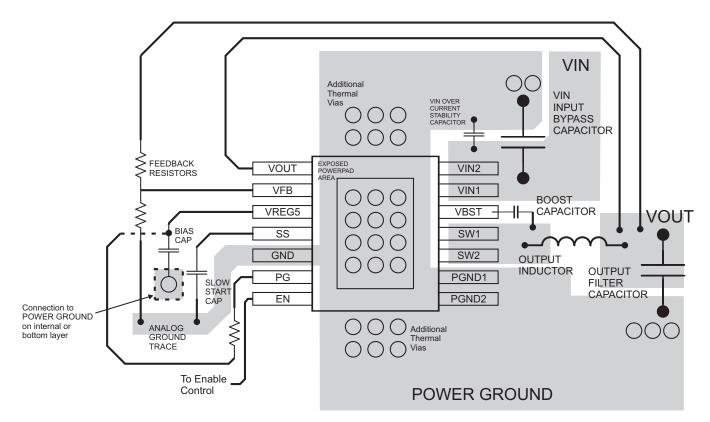
Figure 15. Thermal Pad Dimensions



LAYOUT CONSIDERATIONS

- · Keep the input switching current loop as small as possible.
- Keep the SW node as physically small and short as possible to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin of the device.
- Keep analog and non-switching components away from switching components.
- Make a single point connection from the signal ground to power ground.
- Do not allow switching current to flow under the device.
- VREG5 capacitor should be placed near the device, and connected PGND.
- Output capacitor should be connected to a broad pattern of the PGND.
- Voltage feedback loop should be as short as possible, and preferably with ground shield.
- Lower resistor of the voltage divider which is connected to the VFB pin should be tied to SGND.
- Providing sufficient via is preferable for VIN, SW and PGND connection.
- PCB pattern for VIN and SW should be as broad as possible.
- VIN Capacitor should be placed as near as possible to the device.
- The top side power ground (PGND) copper fill area near the IC should be as large as possible. This will aid in thermal dissipation as well lower conduction losses in the ground return
- Exposed pad of device must be connected to PGND with solder. The PGND area under the IC should be as large as possible and completely cover the exposed thermal pad. The bottom side of the board should contain a large copper area under the device that is directly connected to the exposed area with small diameter vias. Small diameter vias will prevent solder from being drawn away from the exposed thermal pad. Any additional internal layers should also contain copper ground areas under the device and be connected to the thermal vias.





- VIA to Ground Plane
- - Etch on Bottom Layer or Under Component

Figure 16. PCB Layout

REVISION HISTORY

Changes from Revision May 2012 (#IMPLIED) to Revision APage• Deleted V_{FBTH} - T_A = 0°C to 85°C, V_O = 1.05 V, continuous mode from the Electrical Characteristics.3• Changed V_{FBTH} - T_A = -40°C to 85°C, V_O = 1.05 V, continuous mode From: MIN = 751 MAX = 779 mV To: MIN = 754 MAX = 776 mV in the Electrical Characteristics3• Changed the Over/Under Voltage Protection section. From: "as the high-side MOSFET driver turns off and the low-side MOSFET turns on" To: "as both the high-side and low-side MOSFET drivers turn off"8



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

www.ti.com

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS54525PWP	ACTIVE	HTSSOP	PWP	14	90	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525	Samples
TPS54525PWPR	ACTIVE	HTSSOP	PWP	14	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	PS54525	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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10-Dec-2020

PACKAGE MATERIALS INFORMATION

www.ti.com 16-Oct-2020

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS54525PWPR	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 16-Oct-2020



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS54525PWPR	HTSSOP	PWP	14	2000	853.0	449.0	35.0

PWP (R-PDSO-G14)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



PWP (R-PDSO-G14) PowerPAD™ SMALL PLASTIC OUTLINE

THERMAL INFORMATION

This PowerPADTM package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



·

Exposed Thermal Pad Dimensions

4206332-2/AO 01/16

NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments



PWP (R-PDSO-G14)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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